

# Silicon Carbide (SiC) MOSFET - EliteSiC, 53 mohm, 1700 V, M1, D2PAK-7L NVBG050N170M1

## Features

- Typ.  $R_{DS(on)} = 53 \text{ m}\Omega @ V_{GS} = 20 \text{ V}$
- Ultra Low Gate Charge (typ.  $Q_{G(tot)} = 107 \text{ nC}$ )
- Low Effective Output Capacitance (typ.  $C_{oss} = 97 \text{ pF}$ )
- 100% Avalanche Tested
- This Device is Halide Free and RoHS Compliant with Exemption 7a, Pb-Free 2LI (on second level interconnection)

## Typical Applications

- Automotive On Board Charger
- Automotive DC-DC Converter for EV/HEV

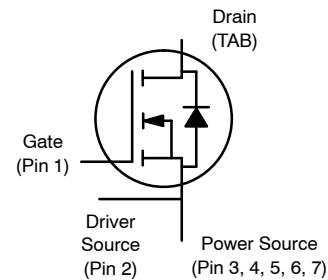
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		$V_{DSS}$	1700	V
Gate-to-Source Voltage		$V_{GS}$	-15/+25	V
Recommended Operation Values of Gate-to-Source Voltage	$T_C < 175^\circ\text{C}$	$V_{GSop}$	-5/+20	V
Continuous Drain Current (Note 2)	Steady State $T_C = 25^\circ\text{C}$	$I_D$	50	A
Power Dissipation (Note 2)		$P_D$	385	W
Continuous Drain Current (Note 2)	Steady State $T_C = 100^\circ\text{C}$	$I_D$	35	A
Power Dissipation (Note 2)		$P_D$	192	W
Pulsed Drain Current (Note 3)	$T_C = 25^\circ\text{C}$ $t_p = 100 \mu\text{s}$	$I_{DM}$	179	A
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$
Continuous Source Current (Body Diode)		$I_S$	87	A
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 22.8 \text{ A}$ , $L = 1 \text{ mH}$ ) (Note 4)		$E_{AS}$	260	mJ
Maximum Lead Temperature for Soldering (1/8" from case for 10 s)		$T_L$	270	$^\circ\text{C}$

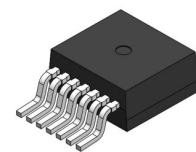
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on a FR-4 board using 1 in<sup>2</sup> pad of 2 oz copper.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
3. Single pulse, limited by max junction temperature.
4.  $E_{AS}$  of 260 mJ is based on starting  $T_J = 25^\circ\text{C}$ ;  $L = 1 \text{ mH}$ ,  $I_{AS} = 22.8 \text{ A}$ ,  $V_{DD} = 120 \text{ V}$ ,  $V_{GS} = 18 \text{ V}$ .

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
1700 V	76 m $\Omega @ 20 \text{ V}$	50 A

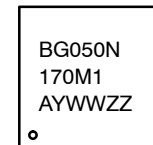


N-CHANNEL MOSFET



D2PAK-7L  
CASE 418BJ

## MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Lot Traceability  
BG050N170M1 = Specific Device Code

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NVBG050N170M1	D2PAK-7L	800 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

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## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case – Steady State (Note 2)	$R_{\theta JC}$	0.39	°C/W
Junction-to-Ambient – Steady State (Notes 1, 2)	$R_{\theta JA}$	40	

## ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	1700			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 1\text{ mA}$ , referenced to $25\text{ }^\circ\text{C}$		0.5		V/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 1700\text{ V}, T_J = 25\text{ }^\circ\text{C}$			100	$\mu\text{A}$
		$V_{GS} = 0\text{ V}, V_{DS} = 1700\text{ V}, T_J = 175\text{ }^\circ\text{C}$ (Note 6)			1	mA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = +25/-15\text{ V}, V_{DS} = 0\text{ V}$			$\pm 1$	$\mu\text{A}$

### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 10\text{ mA}$	1.8	3.1	4.3	V
Recommended Gate Voltage	$V_{GOP}$		-5		+20	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 20\text{ V}, I_D = 35\text{ A}, T_J = 25\text{ }^\circ\text{C}$		53	76	m $\Omega$
		$V_{GS} = 20\text{ V}, I_D = 35\text{ A}, T_J = 175\text{ }^\circ\text{C}$ (Note 6)		107		
Forward Transconductance	$g_{FS}$	$V_{DS} = 20\text{ V}, I_D = 35\text{ A}$ (Note 6)		18		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 1000\text{ V}$ (Note 6)		2078		pF
Output Capacitance	$C_{OSS}$			97		
Reverse Transfer Capacitance	$C_{RSS}$			7.7		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -5/20\text{ V}, V_{DS} = 1000\text{ V}, I_D = 35\text{ A}$ (Note 6)		107		nC
Threshold Gate Charge	$Q_{G(TH)}$			7.6		
Gate-to-Source Charge	$Q_{GS}$			31		
Gate-to-Drain Charge	$Q_{GD}$			25		
Gate-Resistance	$R_G$	$f = 1\text{ MHz}$		2.2		$\Omega$

### SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5/20\text{ V}, V_{DS} = 1200\text{ V}, I_D = 35\text{ A}, R_G = 3.9\text{ }\Omega$ inductive load (Notes 5, 6)		14		ns
Rise Time	$t_r$			22		
Turn-Off Delay Time	$t_{d(OFF)}$			44		
Fall Time	$t_f$			13		
Turn-On Switching Loss	$E_{ON}$			803		$\mu\text{J}$
Turn-Off Switching Loss	$E_{OFF}$			198		
Total Switching Loss	$E_{tot}$			1001		

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## ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b> (continued)						
Continuous Drain-Source Diode Forward Current	$I_{SD}$	$V_{GS} = -5\text{ V}, T_J = 25\text{ }^\circ\text{C}$			87	A
Pulsed Drain-Source Diode Forward Current (Note 3)	$I_{SDM}$				463	
Forward Diode Voltage	$V_{SD}$	$V_{GS} = -5\text{ V}, I_{SD} = 35\text{ A}, T_J = 25\text{ }^\circ\text{C}$		4.3		V
Reverse Recovery Time	$t_{RR}$	$V_{GS} = -5/20\text{ V}, I_{SD} = 35\text{ A}, dI_S/dt = 1000\text{ A}/\mu\text{s}$ (Note 6)		27		ns
Reverse Recovery Charge	$Q_{RR}$			233		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5.  $E_{ON}/E_{OFF}$  result is with body diode.

6. Defined by design, not subject to production test.

TYPICAL CHARACTERISTICS

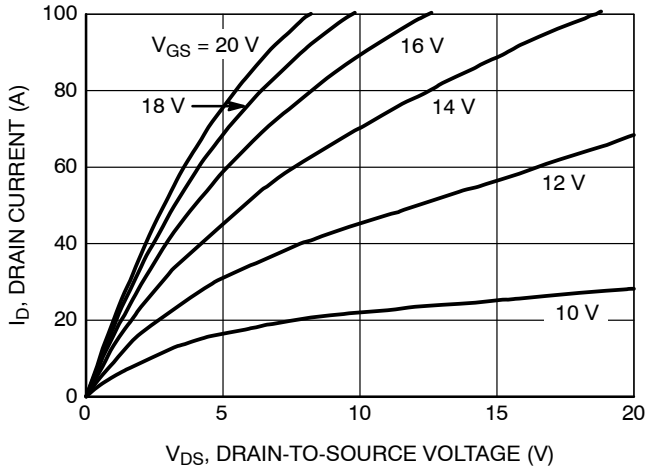


Figure 1. On-Region Characteristics

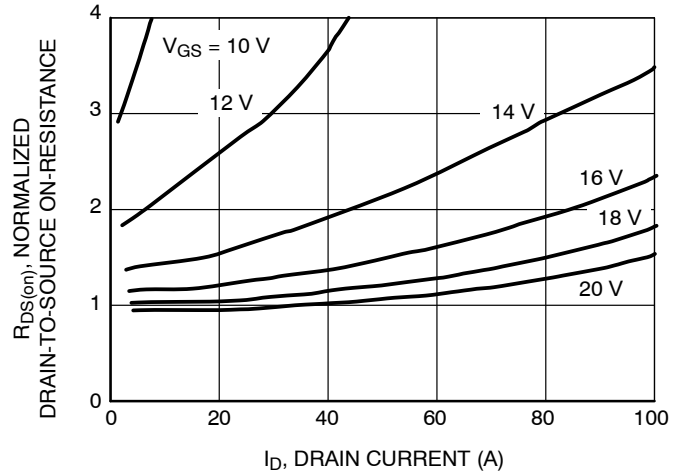


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

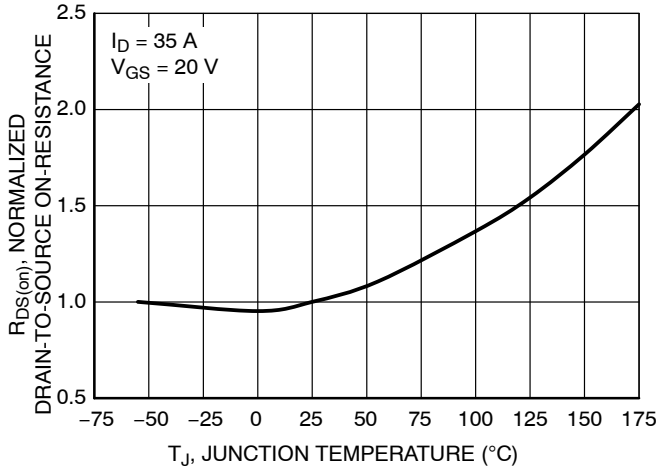


Figure 3. On-Resistance Variation with Temperature

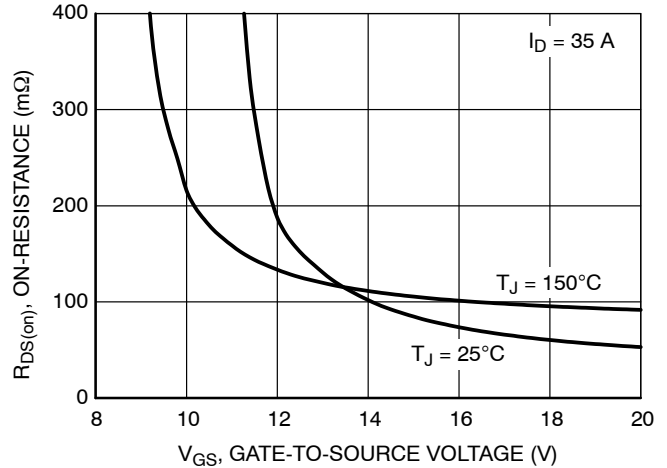


Figure 4. On-Resistance vs. Gate-to-Source Voltage

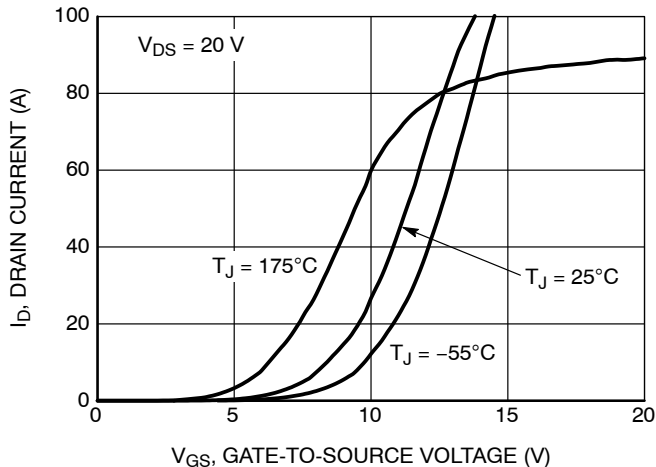


Figure 5. Transfer Characteristics

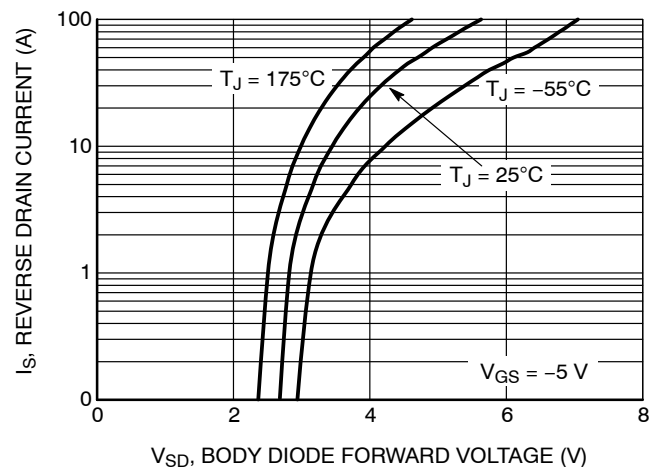


Figure 6. Diode Forward Voltage vs. Current

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## TYPICAL CHARACTERISTICS

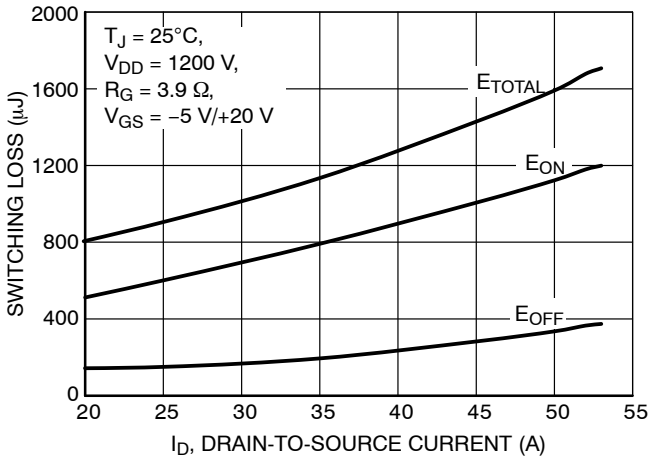


Figure 7. Switching Loss vs. Drain-to-Source Current (25 °C)

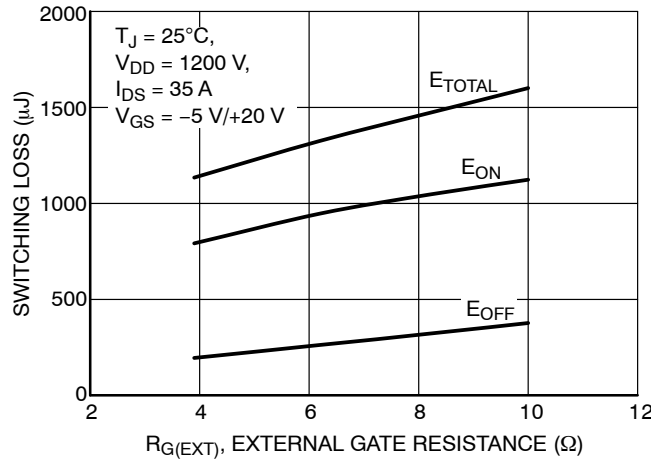


Figure 8. Switching Loss vs. External Gate Resistance

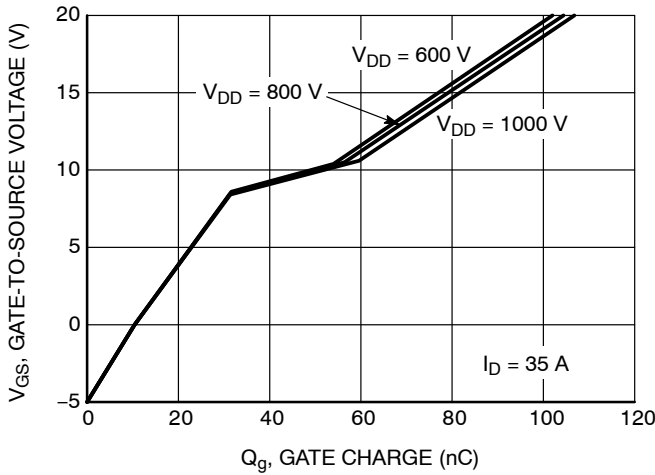


Figure 9. Gate-to-Source Voltage vs. Total Charge

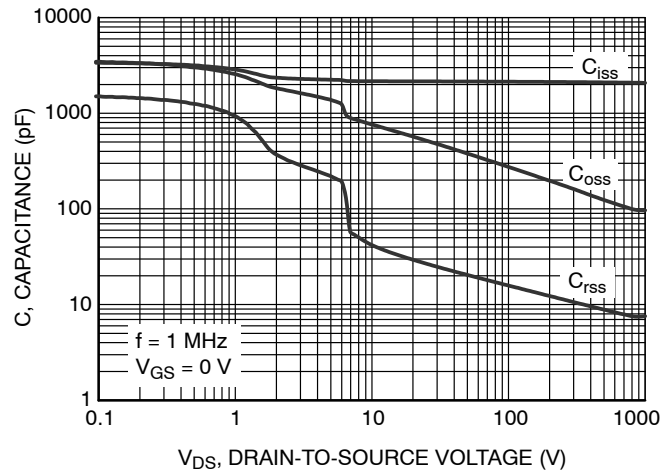


Figure 10. Capacitance vs. Drain-to-Source Voltage

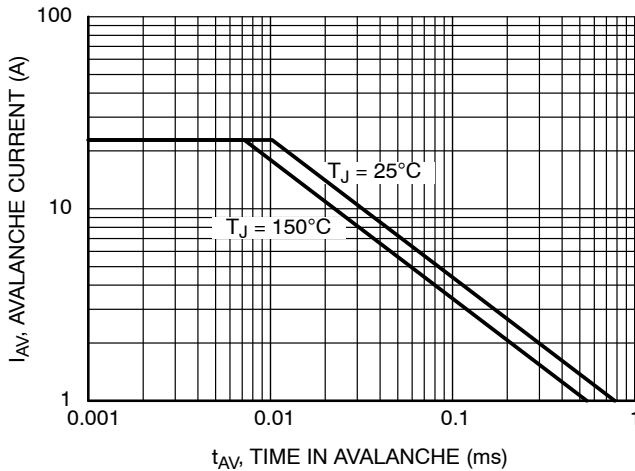


Figure 11. Unclamped Inductive Switching Capability

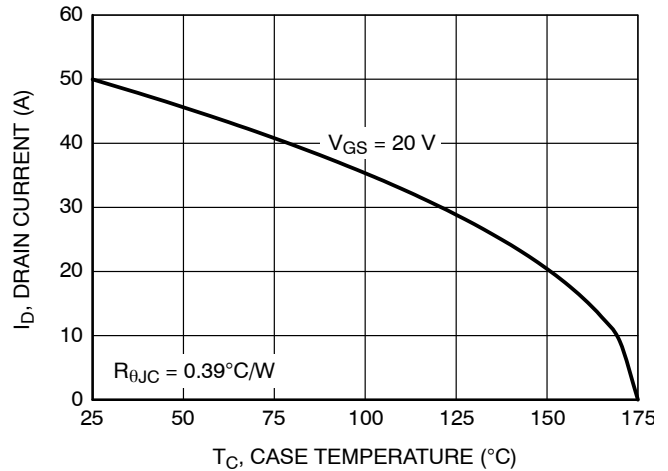
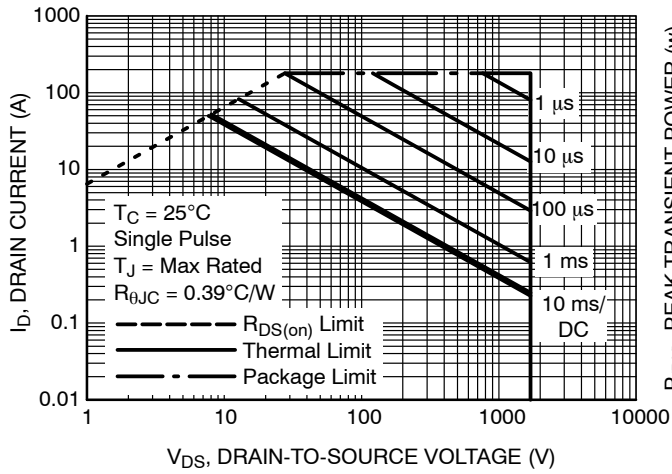


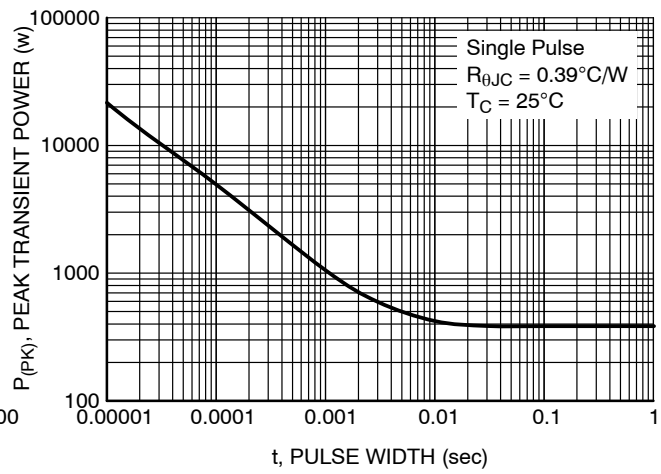
Figure 12. Maximum Continuous Drain Current vs. Case Temperature

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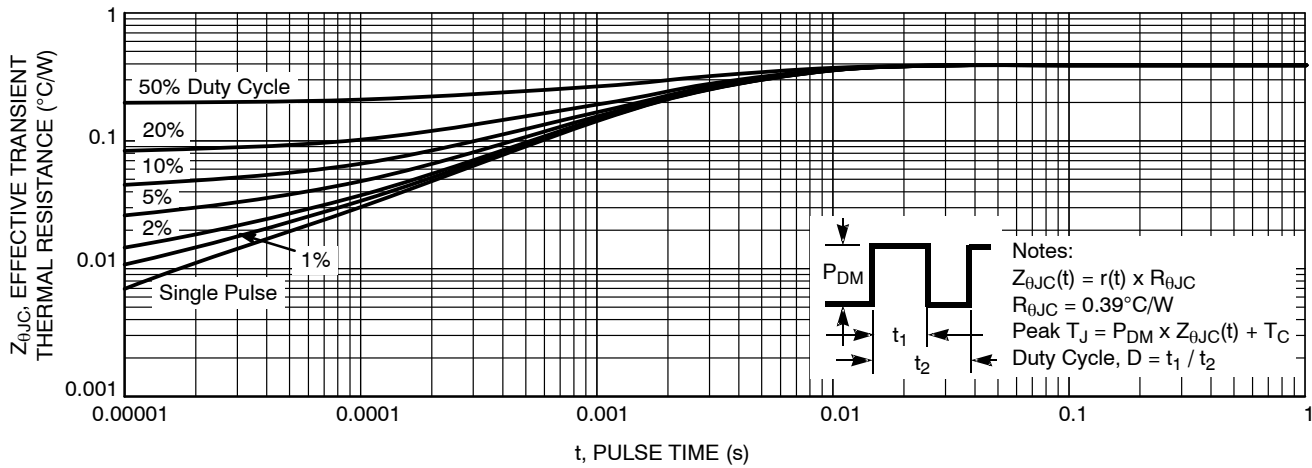
## TYPICAL CHARACTERISTICS



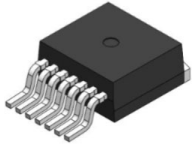
**Figure 13. Maximum Rated Forward Biased Safe Operating Area**



**Figure 14. Single Pulse Maximum Power Dissipation**

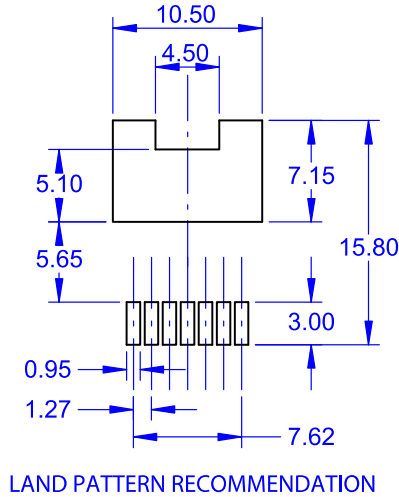
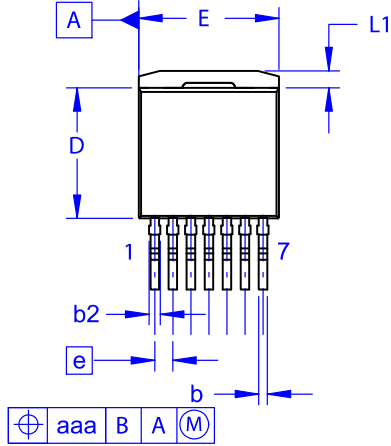


**Figure 15. Transient Thermal Impedance**



**D<sup>2</sup>PAK7 (TO-263-7L HV)**  
CASE 418BJ  
ISSUE B

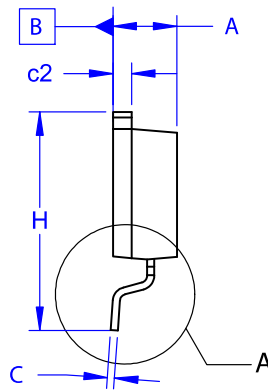
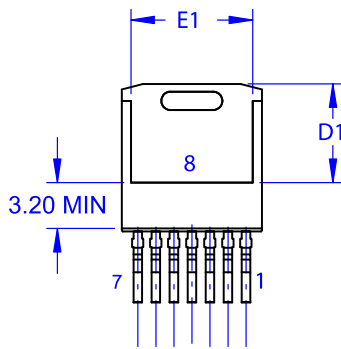
DATE 16 AUG 2019



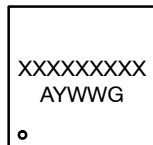
NOTES:

- A. PACKAGE CONFORMS TO JEDEC TO-263 VARIATION CB EXCEPT WHERE NOTED.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. OUT OF JEDEC STANDARD VALUE.
- D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- E. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	0.00	0.10	0.20
b2	0.60	0.70	0.80
b	0.51	0.60	0.70
c	0.40	0.50	0.60
c2	1.20	1.30	1.40
D	9.00	9.20	9.40
D1	6.15	6.80	7.15
E	9.70	9.90	10.20
E1	7.15	7.65	8.15
e	~	1.27	~
H	15.10	15.40	15.70
L	2.44	2.64	2.84
L1	1.00	1.20	1.40
L3	~	0.25	~
aaa	~	~	0.25

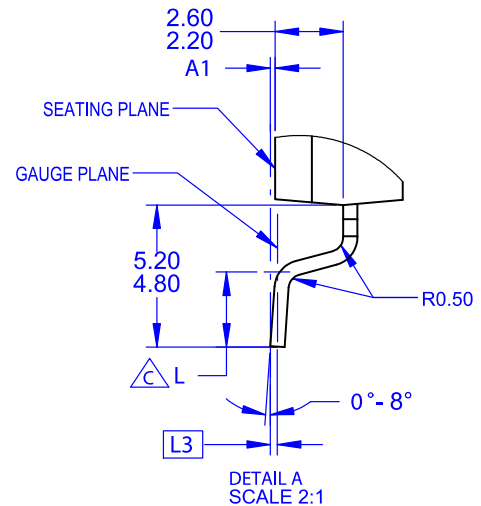


**GENERIC MARKING DIAGRAM\***



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



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